## **Curriculum & Syllabus**

of

## **M.Tech. Nanoscience and Technology**

(For the batches admitted in 2008-09 and 2009-10)



## K.S.RANGASAMY COLLEGE OF TECHNOLOGY TIRUCHENGODE – 637 215

(An Autonomous Institution affiliated to Anna University of Technology Coimbatore and approved by AICTE New Delhi)

K.S. Rangasamy Colle Autonomous	• • •	R 2008
Department	Nanoscience and Te	echnology
Programme Code & Name	51 : M.Tech. Nanoso Technology	

	K.S. Ranga	samy College of Tech	nolog	yy, Tiru	ucheng	gode 637 2	15		
	Currice	lum for the programs	under	Autonc	mous	Scheme			
Regulation		R 2008							
Department		Department of Nanos	cience	and T	echno	logy			
Program Code	& Name	51 : M.Tech. Nanosci	ence a	and Te	chnolo	gy			
-		Seme	ster I						
Course Code	Cours	se Name		Hours/ Week		Credit	Ма	aximum	Marks
			L	Т	Ρ	С	CA	ES	Total
THEORY									
08510101C	Applied Numerical Methods		3	1	0	4	50	50	100
08510102C	Introduction to Qu	antum Concept	3	1	0	4	50	50	100
08510103C	Technology	no Scale Science &	3	0	0	3	50	50	100
08510104C	Advanced Materia	ls Technology	3	1	0	4	50	50	100
08510105C	Introduction of Bio	materials	3	0	0	3	50	50	100
08510106C	Computer Program	nme in C and C++	3	0	0	3	50	50	100
		PRACT	ICAL						
08510107P	Synthesis of Nano	materials Laboratory	0	0	3	2	50	50	100
		Total	18	3	3	23		700	
		Semes	ster II						
Course Code	Cours	se Name		Hours/ Week		Credit	Ма	aximum	Marks
			L	Т	Р	С	CA	ES	Total
		THEC	DRY						
08510201C	Advanced Charac	terisation Techniques	3	1	0	4	50	50	100
08510202C	Nanomaterials and	d Nanomedicine	3	0	0	3	50	50	100
08510203C	Industrial Nanotec	hnology	3	0	0	3	50	50	100
08510204C	Nanoelectronics		3	1	0	4	50	50	100
08510205C	Nanolithography		3	0	0	3	50	50	100
08510206C	Advanced Nanobi	otechnology	3	0	0	3	50	50	100
		PRACT	ICAL						
08510207P	Characterisation c Laboratory		0	0	3	2	50	50	100
08510208P *	Technical Report Presentation I	Preparation and	0	0	2	0	100	00	100
		Total	18	2	5	22		800	

\* This course is applicable only for the students who joined in the year 2009-2010 onwards

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	Curric	ulum for the programs	under	Autonc	omous	Scheme			
Regulation		R 2008							
Department		Department of Nanos	cience	and T	echno	logy			
Program Code	& Name	51 : M.Tech. Nanosci	ence a	and Te	chnolo	ду			
		Semes	ter III						
Course Code	Cour	se Name		Hours/ Week		Credit	Ma	aximum l	Marks
			L	Т	Р	С	CA	ES	Total
		THEC	DRY						
08510301C	Nanodevices		3	0	0	3	50	50	100
085103**E	Elective I		3	0	0	3	50	50	100
085103**E	Elective II		3	0	0	3	50	50	100
		PRACT	ICAL						
08510304P	Project Work - Ph	ase I	0	0	12	6	100	00	100
08510305P	Technical Report Presentation II *	Preparation and	0	0	2	0	100	00	100
		Total	9	0	14	15		500	
		Semes	ter IV						
Course Code	Cour	se Name		Hours/ Week		Credit	Ma	aximum l	Marks
			L	Т	Р	С	CA	ES	Total
08510401P	Project Work - Ph	ase II	0	0	40	20	50	50	100
		Total	0	0	40	20		100	-

	K.S. Ranga	samy College of Tech	nnolog	ıy, Tiru	ucheng	gode 637 2	15		
	Curric	ulum for the programs	under	Autonc	omous	Scheme			
Regulation		R 2008							
Department		Department of Nanos	cience	and T	echno	logy			
Program Code	& Name	51 : M.Tech. Nanosc	ence a	and Te	chnolo	ду			
Course Code	Cour	se Name		Hours/ Week		Credit	Ma	aximum	Marks
			L	Т	Р	С	CA	ES	Total
		Electi	ves l						
08510341E	Micro Electro Mec (MEMS) and Nand System (NEMS)	hanical System o Electro Mechanical	3	0	0	3	50	50	100
08510342E	Nano Biophysics		3	0	0	3	50	50	100
		Electiv	/es II						
08510351E	Nanosafety and E	nvironmental Issues	3	0	0	3	50	50	100
08510352E	Intellectual Proper	ty Rights	3	0	0	3	50	50	100

	K. S. R	angasamy College of	Technology -	Auton	omous	Regu	ation		R 20	800
Dep	partment	Nanoscience and Technology	Program	code &	Name		51 : M.T		lanoscien nology	ce and
			Se	emestei	·I					
Col	urse Code	Course Nar	mo	Ho	urs / We	ek	Credit	Ν	/laximum l	Marks
				L	Т	Р	С	CA	ES	Total
08	510101C	APPLIED NUMERICA METHODS		3	1	0	4	50	50	100
Ob	ijective(s)	With the present deve algorithms for solving complete procedure numerically. At the concepts in numerica	problems in for solving end of the co	science differer ourse t	e, engine It kinds he stud	eering	and techn problems t	ology. hat oc	This cour cur in e	se gives a ngineering
1	SOLUTIO	N OF EQUATION					Total Hrs		09	
Bise	ection Meth	od - Method of False Po	osition, Iteratio	n Meth	od, Seca	ant Me	thod and N	/luller's	Method.	
2	SOLUTIO	N OF EQUATION AND	EIGEN VALU	E PRO	BLEM		Total Hrs		09	
	hod, Gauss symmetric	on of Linear Systems: s - Seidal iteration Metho Tridiagonal Matrix, Hou	od, Solution of seholder Meth	<sup>-</sup> Tridiag	jonal Sy	stems				
3	DIFFERE	ALUE PROBLEMS FOR NTIAL EQUATIONS	-				Total Hrs		09	
Met	hods. Boun	's Method of Successive	Finite Differend	ce Meth	od, Sho					
4	PARTIAL	RY VALUE PROBLEMS	TIONS				Total Hrs		09	
Нур	Laplac erbolic Equ	e's Equation: Jacobi's uations.	Method, Gau	ss-Seid	al Meth	od Al	DI method,	Parab	olic Equa	tions, and
5		CAL INTEGRATIONS					Total Hrs		09	
qua	drature for	grations by Trapezoid mulas, Double intergra Method, Galerkin Metho	des using tra							
	al hours to b								45	
Ref	erence(s) :									
1	S.S. Sasti	ry, "Introductory Method	s of Numerica	I Analys	sis", Pre	ntice-	Hall of India	a, PVT.	LTD,	
2	Internation	n, S.R.K. Iyenkar and nal Limited Wiley Easter	n Limited, Nev	w Delhi	, 1995.					0
3	Delhi, 200									,
4	Khanna P	val, "Numerical Method Publishers, New Delhi, 2	003.	Ū.			•			C & C++",
5		amurthy and N.Ch.S.N.								
6		igam, A. Thangapandi Publications (India) PV				Iram,	"Numeric	Methoo	ds Secon	d Edition",

	K.S. Ra	ngasamy College of T	echnology -	Autono	omous	Regul	ation		R 20	08
Dep	artment	Nanoscience and Technology	Program	code &	Name		51 : M.T	ech - Na Techn	anoscienc ology	e and
			S	emester						
Col	urse Code	Course Nan	20	Hou	rs / We	ek	Credit	М	aximum N	Marks
00			-	L	Т	Р	С	CA	ES	Total
	510102C	INTRODUCTION TO CONCEPT		3	1	0	4	50	50	100
Ob	jective(s)	Impart the basic kn parameters like oper approximate method materials.	ator, Ĕigen i	function,	angula	ar mo	nentum, th	ne varia	tion prind	ciples and
1	INTRODU	CTION					Total Hrs		9	
parti	cle - The ur	ssical physics - Plank' ncertainty principle - So onic oscillator - rigid roto	hrodinger's							
2	WAVE ME	CHANICS					Total Hrs		9	
sphe func 3 The	erically sym tions. OPERATC angular mo	quations in motion - metric potential - hyd PRS AND COMPUTATI mentum operators - E	drogen atom ON LAWS igen values a	- Hydr and Eige	ogen ogen ogen ogen ogen ogen ogen ogen	tions c	<ul> <li>Metrics</li> <li>Total Hrs</li> <li>f Land L -</li> </ul>	repres	entations	ofwave
angu 4		tum – Addition of angul N PRINCIPLES	ar momenta ·	- Clebsi	I - Gold	an co	Total Hrs	Jomput	<u>9</u>	
The	variation pr	inciple - Variation meth orders perturbation – H					state of He		/drogen n	nolecule –
5	APPROXI	MATION METHODS					Total Hrs		9	
Neg	ative energy	quation - particle in a co / states - Magnetic mor s atoms - Hatree equati	ment of the e	lectron -	Radial	equat				
Tota	I hours to b	e taught							45	
Refe	erence(s) :									
1		ass, "Quantum Mechan								
2	New Delhi,							McGra	w Hill pu	blications,
3		"Quantum Mechanics"								
4		d Lokanathan "Quantur					pany of Ind	a Ltd 19	975.	
5	Amit Gosw	ami, "Quantum Mechar	nics" WCBn	uhlishar	1002					

	K.S. Ra	ingasamy College of	f Technology	- Auton	omous	Regu			R 20	
Dep	artment	Nanoscience and Technology	Program	code &	Name		51 : M.T	Fech - Na Techn	anoscienc ology	e and
				Semeste	ər I					
Car	rse Code	Course Na		Hou	irs / We	ek	Credit	М	aximum N	/larks
Cou	ise Code	Course Na	ame	L	Т	Р	С	CA	ES	Total
085	510103C	INTRODUCTION C SCALE SCIENCE TECHNOLOGY	&	3	0	0	3	50	50	100
Obj	jective(s)	Impart the basic process technique knowledge on the Acquire the knowledge Study the reactive	es available exotic proper edge above t	for the ties of r he varic	proces nanostru ous nan	ssing ictured opartic	of Nanos I materials cles proces	tructurec at their	l materia nanosca	ls. Impar le lengths
1	INTRODU					· ·	Total Hrs		9	
mole		olutions – Types o phase Energy-Mole								
2	NANOMA	TERIAL SYNTHESIS	METHODS				Total Hrs		9	
prepa	aration -	Nano scale materia mechanical grinding, processing, chemical v	wet chemica	I synthe	sis – so	ol-gel	processing	, gas pł	nase synt	
3		TERIAL PROPERTIE					Total Hrs		9	
		the nano scale - Leng ar forces-Evolution of					gy landsca	pes-Inter	<sup>,</sup> dynamic	aspects
4	QUANTU	M DOTS AND NANO	TUBES				Total Hrs		9	
	ano mach	<ul> <li>Nano wires-Nano t ines-biological memb</li> </ul>	ranes.			and m	nesopores,	micelles	s, bilayers	, vesicles
5	MATERIA						Total Hrs		9	
effec quan	ts on stre tum wires	no structuring on Me ngth of metals optica and carbon nano t try of tailored monola	al properties ubes-magneti	of quant c behav	tum dot	s and	quantum	wires-ele	ectronic tr	ansport ir
Tota	I hours to b	be taught							45	
Refe	rence(s):									
1	technolog	son, Kamali Kannar ies", Overseas Press	, 2005.							Emerging
2		. Poole, Frank J. Owe					-			
3	Mark A. F	atner, Daniel Ratner,	"Nanotechno	loav: A d	nentle in	troduc	tion to the	next Big	Idea" Pr	entice Hal

	K.S. Ran	gasamy College of	Technology	- Auton	omous	Regu	lation		R 20	800
Depar	tment	Nanoscience and Technology	Program	code &	Name		51 : M.T	Fech - Na Techn	anoscieno ology	ce and
				Semeste	er I					
Course	e Code	Course Na	mo	Hou	rs/We	ek	Credit	М	aximum N	Marks
Course	e Code	Course Na	ame	L	Т	Р	С	CA	ES	Total
08510	0104C	ADVANCED MATE TECHNOLOGY	RIALS	3	1	0	4	50	50	100
	tive(s)	Understand the b properties and va material.etc. Impai memory alloys and	arious applic rt the knowle acquire the v	ations c dge abc	of diele out the	ctric i new i chemic	naterials naterials I al properti	magneti ike sma	c, super rt materi	conducting als, shape
		IRE & BONDS OF S					Total Hrs		9	
Introduc crystal s Imperfe	ction-Latt systems ·	s-dipole bonds-hydro ice Points-Space la - simple cubic - body nt defect-Vacancy- al lattice.	attice-basis - / centered-Fa	crystal ce cente	structur red -he>	e-unit kagona	l-crystal s	ymmetry	-Miller inc	dices.
							Total Hrs		9	
Dielectr Dipolar	ric Loss-le relaxatio	electricity-Properties onic Polarizability as n-Effects of Dielectri	s a function o			nplex o	dielectric c		of Non-po	
		CMATERIALS			_		Total Hrs		9	
suscept	tibility of a	als: Dia and Parama conduction electrons	-Ferro-anti fe	rromagn						ramagnetic
4 M	ATERIAL						Total Hrs		9	
confine	ment-qua	g materials: Semicor antum wires and d e polymers.								
5 N	EW MAT	ERIALS					Total Hrs		9	
		Smart materials-sh rties-processing-text			shape r	nemor	y effects-	Martens	sitia Tran	sformation
Total ho	ours to be	e taught							45	
Referer	nce(s) :									
1 V.	Rajendra	an, Material Science	, Tata McGra	w Hill, Ne	ew Delh	ni, 2009	).			
2 A.	J. Dekke	r, Solid state Physic	S.							
3 S.	O. Pillai,	Solid state Physics,	2007 Revised	d Edition						
		troduction to Solid S								
5 Fi	unakuho	Shape Memory Alloy	/s, Gorden an	d Breach	n, New `	York, 1	984.			

K.S. F	Rangasamy College of T	echnology - Au	tonom	ous R	egulat	ion		R 20	08
Department	Nanoscience and Technology	Program co	de & N	lame		51 : M.T	ech - Na Techn	anoscien ology	ce and
		Seme	ster I						
Course Code	Course Na	amo	Ηοι	urs / We	eek	Credit	M	aximum I	Marks
		ame	L	Т	Р	С	CA	ES	Total
08510105C	INTRODUCTION OF BIOMATERIALS		3	0	0	3	50	50	100
eObjective(s)	Understand the basic knowledge about Characterisation tech biomaterials for impla	DNA nanotechr niques related to	nology	and	nano	sensors	and	understar	nd basic
1 INTRODU	JCTION	••			٦	otal Hrs		9	
	nd biological materials- e ring biomaterials- pure m						als-Gen	eral chara	acteristics
	GENERATION BIOMAT	-				otal Hrs		9	
Second gener polymers-hydr	ation bio materials and o gels.	their properties -	Bioad	tive an	nd biod	degradabl	e ceran	nics-biod	egradable
3 THIRD G	ENERATION BIOMATER	RIALS			٦	otal Hrs		9	
conjugates-mic	on biomaterials - Chara cro array technologies erials, molecular motors b	-Micro nanotec	hnolog	y mic	ro fa				gate DNA between
4 NANOBIO	DTECHNOLOGY				٦	otal Hrs		9	
nano probes f	NA nanotechnology-strue or analytical applications osensors of the future.								
5 MICROS						otal Hrs		9	
molecules spe	dern - Advances-micro ctroscopy- single molec puter-PCR amplification	ule DNA detection	on, so	rting, s	equen	cing-DNA			
Total hours to	be taught							45	
Reference(s) :									
	al, "Nanoscale Technolo								
	myer & C.A. Mirkin, "Nar MBH & Co, 2004.	nobiotechnology:	Conce	epts, Ap	oplicat	ions and	Perspec	ctives", V	Viley VCH
3 Joon B. F	Park, R.S. Lakes, "Bio Ma	aterials: An Introc	duction	", Birkh	läuser	2 <sup>nd</sup> Editio	on 1992		
4 Advances	s in biomaterials, drug de	livery and Bionar	notechr	nology-	AICHE	.J 2003,	49(12):	2990-300	06.

	K.S. Ra	ngasamy College of 1	echnology - Au	tonom	ious R	egulat	ion		R 20	800
Depa	artment	Nanoscience and Technology	Program co	de & N	lame		51 : M.T	ech - Na Techn		ce and
			Seme	ster I						
Court	raa Cada	Course Na		Ηοι	urs / W	eek	Credit	Ma	aximum l	Marks
Cour	rse Code	Course Na	ame	L	Т	Р	С	CA	ES	Total
085	510106C	COMPUTER PROGR AND C++		3	0	0	3	50	50	100
Obje	ective(s)	Impart the basic progr	amming in C & C	C++.						
1 I	BASIC COI	NCEPTS IN C				٦	otal Hrs		9	
Outpu	ut – Contro	Keywords - Constant V I Structures – if and Sv ter strings – Simple pro	vitch statements							
		I & POINTERS				Total		9		
		unctions - Defining and nter Declarations – Pas							tions pro	ototypes -
3	STRUCTU	RE & ARRAYS				Total	Hrs	9		
		ta types - Structures - sequential file processi					g membe	ers – Ari	ay of st	ructures -
4 I	BASIC COI	NCEPTS IN C++				Total	Hrs	9		
decla	ration – D	Programming (OOP) - ifferences between C ects – Constructors and	and C++ - Fund	ctions .	in C++	- Fu	nction ov	erloadin	g/polymo	
5	TYPES OF	CLASSES				Total	Hrs	9		
		es - Inheritance and cts and derived classes			el, mul	tilevel,	multiple	and hy	brid inhe	eritance –
Total	hours to be	e taught						45		
Refer	rence(s) :									
1	E. Balaguru	usamy, "Object – Orient	ed Programming	with C	C++", T	ata Mo	:Graw – H	lill		
		ore, "Object-Oriented P								
	W. Kernigh India.	an Brain and M. Ritchi	e Dennis, "The C	C Prog	rammir	ig Lan	guage", 2	<sup>nd</sup> Editic	on, Prent	ice Hall of
4 I	Bjarne Stro	ustrup, "Programming:	Principles and p	ractice	using (	C++:, /	Addison-V	Vesley p	orofessio	nal.

K.S. Ra	ngasamy College	of Technology - A	utono	mous	Regulation			R 2008	
Department	Nanoscience and Technology	Program code	e & Nar	ne	51 :	M.Tech Te	<ul> <li>Nanoso chnology</li> </ul>		nd
		Ser	nester	I					
Course Code	Cours	e Name	ł	Hours /	Week	Credi t	Max	imum N	larks
			L	Т	Р	С	CA	ES	Total
08510107P	SYNTHESIS OF NANOMATERIA LABORATORY		0	0	3	2	50	50	100
Objective(s)		different methods . Study the vario							
<ol> <li>Prepara</li> <li>Prepara</li> <li>Prepara</li> <li>Prepara</li> <li>Synthe</li> <li>Effect of</li> <li>Synthe</li> <li>Imaging</li> </ol>	ation of nanoparticl ation of nanoparticl ation of nanoparticl sis of nano compos of particle size on P	site materials – Spra hysical / Chemical µ s – Spray Pyrolyse	l Reactor ay Pyro properti	lyser					
F	5				Т	otal Hrs		45	

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Dep	partment	Nanoscience and Technology	Program code & Na	ame	51 :	M.Te	ch - Nano	oscienc	e and T	echnology
			Semeste	er II						
Co	urse Code	Co	urse Name	Hou	rs / We	ek	Credit	М	aximum	Marks
		00		L	Т	Ρ	С	CA	ES	Total
	510201C	TECHNIQUES	IARACTERISATION	3	1	0	4	50	50	100
Ot	ojective(s)	knowledge abo	<ul> <li>relative methods of ut the different characte techniques and study e ique.</li> </ul>	risatior	n techn	iques	. Impart t	the kno	wledge	about the
1	OPTICAL	MICROSCOPY				Т	otal Hrs		9	
Opti			spectroscopy - Basics	- AAS	– ICP			n Micr	oscopy:	Scanning
colle	ection in el	ectron microscope	ion electron microscopy s – Environmental trans ale – In-situ nano meas	smissio	n elect					
2	SCANNIN	IG PROBE MICRO	SCOPY			Т	otal Hrs		9	
Opti	cal microso	copy - Confocal m	omic manipulations – Ato nicroscopy – Scanning isted laser desorption ion	near fie	eld opti	ical m	icroscopy	y – Se	condary	ography – ion mass
3	SPECTRO	DSCOPY				Tota	l Hrs		9	
JUE			Evoitone Infrared ou	rfaga a	nootroc	oonv	Domor	cnoot	· · · · · · · · · · · · · · · · · · ·	Drillouin
spec spec	ctroscopy - ctroscopy -	- Dynamic Light S	– Excitons – Infrared su Scattering (DLS) – NM etric Analysis (TGA) –	R Spec	ctrosco	ру —	ESR spe	ectrosc	opy – ľ	Mossbauer
spec spec	ctroscopy - ctroscopy - hanical An	- Dynamic Light S - Thermo gravime	Scattering (DLS) – NM etric Analysis (TGA) –	R Spec	ctrosco	py – canni	ESR spe	ectrosc	opy – ľ	Mossbauer
spec spec mec 4 Mec hard	troscopy - troscopy - <u>hanical An</u> MECHAN hanical Ch hanical Ch	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravime alysis (TMA).</li> <li>ICAL CHARACTEF</li> <li>naracterization – N</li> <li>tigue – Abrasion a</li> </ul> </li> </ul>	Scattering (DLS) – NM etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – S	R Spec Differe ing ca	ctrosco ntial S pability asticity	py – canni Tota of n – Na	ESR spe ng Calor I Hrs ano regio	ectrosc imetry on/ cor tation -	opy – M (DSC) 9 npressio	Mossbauer – Thermo on - micro tribology –
spec spec mec 4 Mec hard	ctroscopy - ctroscopy - hanical An MECHAN hanical Ch hanical Ch lness – Fa o tribometr	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravime alysis (TMA).</li> <li>ICAL CHARACTEF</li> <li>naracterization – N</li> <li>tigue – Abrasion a</li> </ul> </li> </ul>	Scattering (DLS) – NM etric Analysis (TGA) – RISATION fodulus and load carry	R Spec Differe ing ca	ctrosco ntial S pability asticity	py – canni Tota of n – Na	ESR spe ng Calor I Hrs ano regio	ectrosc imetry on/ cor tation -	opy – M (DSC) 9 npressio	Mossbauer – Thermo on - micro tribology –
spec spec 4 Mec hard Nan 5 Neu crys - Th	troscopy - troscopy - hanical An MECHAN hanical Ch lness – Fa o tribometr DIFFRAC tron and X tallography hermo lumi	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravime alysis (TMA).</li> </ul> </li> <li>ICAL CHARACTEF naracterization - N tigue - Abrasion a e - Surface Force for the surface Force for the surface for</li></ul>	Scattering (DLS) – NM etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – S	R Spec Differe ing ca uper pl tal micr – Disk utron so e (XAF	pability ocation catterin	py – canni Tota of n – Na ce – Tota dens g in r	ESR spe ng Calor I Hrs ano regio no indem Friction fo I Hrs sity – Mic ano scier	ectrosc imetry on/ cor tation - rce mid ro strai nce - P	opy – N (DSC) 9 npressio - Nano croscop 9 n macro hotolum	Mossbauer – Thermo on - micro tribology – e. omolecular inescence
spec spec 4 Mec harc Nan 5 Neu crys - Tr (EX/	troscopy - troscopy - hanical An MECHAN hanical Ch lness – Fa o tribometr DIFFRAC tron and X tallography hermo lumi	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravime alysis (TMA).</li> </ul> </li> <li>ICAL CHARACTEF naracterization – N tigue – Abrasion a e – Surface Force force for a diffraction – I for using synchrotron nescence – X-ray actron scattering for</li> </ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – Si apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur	R Spec Differe ing ca uper pl tal micr – Disk utron so e (XAF	pability ocation catterin	py – canni Tota of n – Na ce – Tota dens g in r	ESR spe ng Calor I Hrs ano regio no indem Friction fo I Hrs sity – Mic ano scier	ectrosc imetry on/ cor tation - rce mid ro strai nce - P	opy – N (DSC) 9 npressio - Nano croscop 9 n macro hotolum	Mossbauer – Thermo on - micro tribology – e. omolecular inescence
spec spec 4 Mec hard Nan 5 Neu crys - Th (EX) Tota	troscopy - troscopy - hanical An MECHAN hanical Ch lness – Fa o tribometr DIFFRAC tron and X tallography hermo lumi AFS) – Ele	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravime alysis (TMA).</li> </ul> </li> <li>ICAL CHARACTEF naracterization – N tigue – Abrasion a e – Surface Force force for a diffraction – I for using synchrotron nescence – X-ray actron scattering for</li> </ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – Si apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur	R Spec Differe ing ca uper pl tal micr – Disk utron so e (XAF	pability ocation catterin	py – canni Tota of n – Na ce – Tota dens g in r	ESR spe ng Calor I Hrs ano regio no indem Friction fo I Hrs sity – Mic ano scier	ectrosc imetry on/ cor tation - rce mid ro strai nce - P	opy – N (DSC) 9 npressio Nano croscop 9 n macro hotolum ption fin	Mossbauer – Thermo on - micro tribology – e. omolecular inescence
spec spec 4 Mec hard Nan 5 Neu crys - Th (EX) Tota	troscopy - troscopy - hanical And MECHAN hanical Ch hanical Ch lness – Fai o tribometr DIFFRAC tron and X tallography hermo lumi AFS) – Elec l hours to b erence(s) :	<ul> <li>Dynamic Light S</li> <li>Thermo gravime alysis (TMA).</li> <li>ICAL CHARACTEF</li> <li>naracterization – N</li> <li>tigue – Abrasion a</li> <li>e – Surface Forces</li> <li>TOMETER</li> <li>ray diffraction – I</li> <li>using synchrotron</li> <li>nescence – X-ray a</li> <li>ctron scattering for</li> <li>be taught</li> </ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – Si apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur	R Spec Differe ing ca uper pl tal micr - Disk utron sc e (XAF A).	pability pability asticity robalan catterin S) – E	py – canni of n – Na ce – Tota dens g in r xtend	ESR spe ng Calor I Hrs ano regio no indem Friction fo I Hrs sity – Mic ano scier	ectrosc imetry on/ cor tation - rce mid ro strai nce - P	opy – N (DSC) 9 npressio Nano croscop 9 n macro hotolum ption fin	Mossbauer – Thermo on - micro tribology – e. omolecular inescence
spec spec 4 Mec harc Nan 5 Neu crys - Tr (EX) Tota Refe	troscopy - ctroscopy - hanical An MECHAN hanical Cr lness – Fa o tribometr DIFFRAC tron and X tallography hermo lumi AFS) – Elev I hours to to erence(s) : T.Pradeep	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravime alysis (TMA).</li> <li>ICAL CHARACTEF</li> <li>Tracterization – N</li> <li>tigue – Abrasion a</li> <li>e – Surface Force a</li> <li>TOMETER</li> <li>ray diffraction – I</li> <li>guing synchrotron</li> <li>nescence – X-ray a</li> <li>ctron scattering for</li> <li>be taught</li> </ul> </li> <li>winano: The Essee</li> </ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – Si apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur chemical Analysis (ESC	R Spec Differe ing ca uper pl tal micu – Dislu utron sc e (XAF ;A).	pability pability asticity robalan ocation catterin S) – E	py – canni Tota of n – Na ce – Tota dens g in r xtend	ESR spe ng Calor I Hrs ano regio no inden Friction fo I Hrs sity – Mic ano scier ed X- ray	ectrosc imetry on/ cor tation - orce mid ro strai nce - P absorp	opy – N (DSC) 9 npressio - Nano croscope 9 n macro hotolum otion fine 45	Mossbauer – Thermo on - micro tribology – e. omolecular inescence e structure
spec spec 4 Mec harc Nan 5 Neu crys - Tr (EX) Tota Refe	troscopy - ctroscopy - hanical An MECHAN hanical Cr lness – Fa o tribometr DIFFRAC tron and X tallography hermo lumi AFS) – Elec I hours to t erence(s) : T.Pradeep Charles P Pulickel M VCH Verla	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravine alysis (TMA).</li> <li>ICAL CHARACTER</li> <li>Taracterization – Maracterization scattering for the scattering for scattering for scattering for the scat</li></ul></li></ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – Sr apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur chemical Analysis (ESC mitials",Tata McGraw Hill k J Ownes, "Introduction Schadler, Paul V.Braun,	R Spec Differe ing ca uper pl tal micr – Disk utron sc e (XAF ;A).	pability pability asticity ocation catterin S) – E Delhi, 2 notechr	py – canni Tota of n – Na ce – Tota dens g in r xtend	ESR speng Calor I Hrs ano region Friction for I Hrs ity – Mic ano sciened X- ray	viley Sond Tech	opy – N (DSC) 9 npressic - Nano croscop 9 n macro hotolum otion fin 45 	Mossbauer – Thermo on - micro tribology – e. omolecular inescence e structure 03. 7, Wiley –
spec spec 4 Mec harc Nan 5 Neu crys - Th (EX) Tota Refe 1 2	troscopy - ctroscopy - hanical An MECHAN hanical Ch lness – Fa o tribometr DIFFRAC tron and X tallography hermo lumi AFS) – Elec I hours to t erence(s) : T.Pradeep Charles P Pulickel M VCH Verla Mick Wils	<ul> <li>Dynamic Light \$         <ul> <li>Thermo gravine alysis (TMA).</li> <li>ICAL CHARACTER</li> <li>Taracterization – Maracterization scattering for the taught</li> <li>Wano: The Essee</li> <li>Poole Jr and Frant</li> <li>Ajayan, Linda S.Sag, weiheim, 2003.</li> <li>Kamali Kanna</li> </ul> </li> </ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – St apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur chemical Analysis (ESC	R Spec Differe ing ca uper pl tal mici – Disk utron sc e (XAF A).	pability pability asticity ocation catterin S) – E Delhi, 2 notechr ocompo	py – canni Tota of n – Na ce – Tota dens g in r xtend 2007. nology psite S	ESR speng Calor I Hrs ano region Friction for I Hrs ity – Mic ano sciened X- ray	viley Sond Tech	opy – N (DSC) 9 npressic - Nano croscop 9 n macro hotolum otion fin 45 	Mossbauer – Thermo on - micro tribology – e. omolecular inescence e structure 03. 7, Wiley –
spec spec mec 4 Mec harc Nan 5 Neu crys - Tr (EX) Tota Refe 1 2 3	ctroscopy - ctroscopy - hanical An- MECHAN hanical Ch lness – Fa- o tribometr DIFFRAC tron and X tallography hermo lumi AFS) – Eler I hours to t erence(s) : T.Pradeep Charles P Pulickel M VCH Verla Mick Wils Basic scie	<ul> <li>Dynamic Light S</li> <li>Thermo gravine alysis (TMA).</li> <li>ICAL CHARACTEF</li> <li>ICAL CHARACTEF</li> <li>ICAL CHARACTEF</li> <li>ICAL CHARACTEF</li> <li>ICAL CHARACTEF</li> <li>Taracterization – N</li> <li>tigue – Abrasion a</li> <li>e – Surface Force</li> <li>TOMETER</li> <li>ray diffraction – I</li> <li>rusing synchrotron</li> <li>nescence – X-ray a</li> <li>ctron scattering for</li> <li>be taught</li> <li>poole Jr and Fran</li> <li>Ajayan, Linda S.S</li> <li>ag, weiheim, 2003.</li> <li>on, Kamali Kanna</li> <li>ences and emerging</li> </ul>	Scattering (DLS) – NMI etric Analysis (TGA) – RISATION Modulus and load carry nd wear resistance – Si apparatus – Quartz crys Debye Scherrer formula radiation – Role for neu absorption Fine Structur chemical Analysis (ESC entials", Tata McGraw Hill k J Ownes, "Introduction Schadler, Paul V.Braun, ungara, Geoff Smith, M	R Spec Differe ing ca uper pl tal mici – Disk utron sc e (XAF A).	pability pability asticity ocation catterin S) – E Delhi, 2 notechr ocompo	py – canni Tota of n – Na ce – Tota dens g in r xtend 2007. nology psite S	ESR speng Calor I Hrs ano region Friction for I Hrs ity – Mic ano sciened X- ray	viley Sond Tech	opy – N (DSC) 9 npressic - Nano croscop 9 n macro hotolum otion fin 45 	Mossbauer – Thermo on - micro tribology – e. omolecular inescence e structure 03. 7, Wiley –

	K.S. Rang	gasamy College of Te	chnology	- Auton	omous	Regu	ulation		R	2008
De	partment	Nanoscience and Technology	Program	n code &	Name		51 : N		Nanosc hnology	ience and
				Semes	ter II					
0				Hou	rs / We	ek	Credit		Maximu	m Marks
Co	urse Code	Course Nar	ne	L	Т	Р	С	CA	ES	Total
30	3510202C	NANOMATERIALS NANOMEDICINE		3	0	0	3	50	50	100
O	ojective(s)	Understand the Nanomaterials in nanosensors. Imp applications and ga applications.	medicine. art the kn	Impar owledge	t knov e to a	vledge pply 1	e about the Nano	drug materia	delivery Is in dit	systems and fferent medical
1	BASIC OF	NANOBIOMOLECUL	ES			-	Total Hrs		ļ	9
Stru of n Cell	cture prope ano bioma ulose and d	erty relationship of Bi rty relationship of tissu terials – Polymeric so erivates – Dextrans –	ues, bones caffolds col Alginates –	and teet llagen –	h - Col - Elasti	lagen ns – 1.	rich tissue Mucopoly	es - elas	ides – F	es - Preparation Proteoglycans -
2		- NANOBIOMOLECUL					Total Hrs			9
part	icle drug sy inistration -	Development of nan stem for oral adminis Nanotechnology in di	tration – D agnostic ap	rug syst	em for	nasal	administ		Drug sy	stem for ocular
3	DNA - NAI	NOBIOTECHNOLOGY	/			-	Total Hrs		ę	9
surfa	aces – Bio	Antibody conjugated medical nanoparticles gradable polymers – A	<ul> <li>Liposon</li> </ul>	ne's — [						
4	NANOSTF	RUCTURED MATERIA	LS IN MED	ICINE		-	Total Hrs		9	9
Che Imm	motherapy	nanoparticles in cance – Active and Passive – Vaccine immunothe eting.	e cancer tis	sue targ	geting ·	- Mic	ro fluidics	- Che	motherap	peutic agents -
5	NANOSEN	ISORS				-	Total Hrs		ę	9
– Ar	nion sensing	nano sensors – Organi g – Surface confined c – Raman sensing at su	hemical se	nsors –	Nanopa	article	s sensors	- Caloi	imetric s	ensing - Vapor
Tota	I hours to b	e taught							4	5
Refe	erence(s) :									
1	J. B Park,	"Biomaterials Science	and Engine	ering", I	Plenum	Pres	s, New Yo	rk, 1984	1.	
2	T. Pradeep	o, "Nano: The essentia	ls" , McGre	w – Hill,	2007					
3		Dekker, "Encyclopedi								
4	Natalie P.	Praetories and Tarun	K. Mandal,	Recent I	Patents	on D	rug Delive	ry& For	mulation	
5	Y. Lu, S.C	. Chen, Advanced Dru	g Delivery I	Reviews						

	K.S. Rar	ngasamy College of Tecl	nnology - A	Autono	mous	Regu	ation		R	2008
Dep	partment	Nanoscience and Technology	Program	n code &	Name	e	51 : N		Nanosc	ience and
			S	Semeste	r II					
0.0				Hou	rs / We	ek	Credit		Maximu	m Marks
00	urse Code	Course Name	;	L	Т	Р	С	CA	ES	Total
	510203C	INDUSTRIAL NANOTECHNOLOGY		3	0	0	3	50	50	100
Ot	ojective(s)	Understand the application various principles and					stries and	d study	the relat	ive methods of
1	SEMICON	NDUCTING NANOPARTIC	CLES			Т	otal Hrs		9	9
		physics - Fabrication tec - Principles and perform								
	cal devices					-		1		
2		IC NANOPARTICLES					otal Hrs			9
nan		agnetism in solids – Pro I magnets - Probes of r eling.								
3	NEMS & I	MEMS				Т	otal Hrs		9	Э
perf	ormance o	no-Electromechanical system of different structures - A gnetic, chemical, and meet	dvantages	and d	isadva	ntage	s of diffe			
4		LAR ELECTRONICS					otal Hrs		(	9
Org	anic electro	<ul> <li>Conjugation – Excitatio oluminescent displays injer r order: excimers - H- and</li> </ul>	ection – Tr	ansport	- Exc	iton fo	rmation -			
5	APPLICA	TION OF NANOPARTICL	ES IN IND	USTRY		Т	otal Hrs		ę	9
		and Micro – Organism, extiles, Paints, Catalysis,						Dentistr	y, Food	and Cosmetic
Tota	al hours to	be taught							4	-5
Refe	erence(s) :									
1	J. Verdey	en, "Laser Electronics", II	Edition, Pre	entice H	all, 19	90.				
2		ner, T. Van Duzer, "Princip								
3		, M.Pomeranty, "Electror ew York, 1991.	esponsive	molecu	iles ar	nd po	lymeric s	systems	", Skoth	eim T. Marcel
4		"Principles of Optical Elec								
5	1995 (ISE	y, M R Bryce, D Bloor (6 N 0-340-58009-7)								
6		oannou, P F van Hutten H, 2000 (ISBN 3-527-2950		nducting	Polyr	ners:	Chemistr	y, Phys	sics, and	d Engineering',
7		radley, Current Opinion in		e & Mate	erials S	Scienc	e Vol. 1, 1	789 (19	96)	

	K.S. Rang	gasamy College of Tech	nnology -	Autono	mous	Regu	lation		R	2008
De	partment	Nanoscience and Technology	Program	n code 8	Name	;	51 : N		Nanosc	ience and
			S	Semeste	r II					
<u> </u>		Course Norma		Hou	rs / We	ek	Credit		Maximu	m Marks
Co	ourse Code	Course Name		L	Т	Р	С	CA	ES	Total
30	8510204C	NANOELECTRONICS		3	1	0	4	50	50	100
O	bjective(s)	Understand the basic about the nanostructur nano semiconductor &	red semico	nducting	g mate	rials.	Understa	nd the		
1		F NANOELECTRONICS				-	otal Hrs			9
inte pro con	racting with cessing - S finement Eff	mentals – Quantization electrons in solids – d ize Effects on structure ects – Fraction of surface	liffusion pr e and Mor e atoms – S	ocesses phology Specific	s – ba v of fre	sic in ee or e ener	formation Supporte gy and su	theory ed Nar	v – data noparticle ntress.	& bits – data es – Size and
2		1 CONCEPTS IN NANOE absorption spectra - BI					otal Hrs			9
nan Artii 3 Nar	ostructures ficial atomic NANOMAT nosystems S	AFM, ISTM tip on a sur (quantum wells) - 1 D i clusters - Size dependen ERIALS PROCESSING ynthesis - Molecular bea position - Ion beam assis	nanostructi nt propertie am epitaxy	ures (qu <u>s.</u> – MOC	iantum VD - C	wires T Chemic	s) OD na otal Hrs cal routes	nostruc	tures (q	uantum dots) - 9 s on polymers -
4		IES OF NANOPARTICLI			J		otal Hrs			9
dots	s - Widening	antum dots - Coulomb blo of band gap in quantum cattering from nano defec	n dots - Str							
5	NANOCON	<b>IPOSITES</b>				Т	otal Hrs		ę	9
nan	oparticles fi	s Electronic and atomic ictionalization processes and model – Switching de	s – Nanoe	electroni	cs wit	h sup	per condu	ucting	devices	
Tot	al hours to b	e taught							4	5
	erence(s) :									
	Keith Barn	ham, Dimitri Dimitrievich applications", Cambridge L			dimens	ional	semicond	luctor s	tructures	: fundamentals
Ref	Keith Barn and device		Iniversity Boo	k, 2001.					tructures	: fundamentals
Ref 1	Keith Barn and device L.Banyai a	applications", Cambridge L	Iniversity Boo Juctor Qua	k, 2001. ntum Do	ots", W	orld S	cientific, <sup>2</sup>	1993.		

	ingasanny conege of reci	hnology - J	Autono	mous	Regu	lation		R	2008
Department	Nanoscience and Technology	Program	n code 8	Name	;	51 : N		· Nanosc chnology	ience and
		S	Semeste	r II		-			
Course Code	e Course Name		Hou	rs / We	ek	Credit		Maximu	m Marks
Course Cours		-	L	Т	Ρ	С	CA	ES	Total
08510205C	NANOLITHOGRAPHY		3	0	0	3	50	50	100
Objective(s)	Understand the basic lithography technique industries and study th	s. Impart	knowled	lge ab	out t	he lithog			
1 BASICS	IN LITHOGRAPHY				Т	otal Hrs		9	9
nanolithograp nanolithograp					desigr	n for elect		ircuits –	Applications of
	L LITHOGRAPHY aphy – Light sources – Pl					otal Hrs			9
ray sources – 3 ION BEA	photo resists – Ultraviolet Synchrotron radiation – X M LITHOGRAPHY ography - Focused ion bea	ray project	ion – X	ray res	ists. T	otal Hrs		-	9
Beam Lithogr	aphy – Ion projection Lith						Doui	III WYIILIII	
vector scan -	Electron proximity / Project						ron opt	tics – Ra	aster scan and
4 MICROL	Electron proximity / Project ITHOGRAPHY	tion Printin	g - Elec	tron re	- sists T	Electron	ron op Beam	tics – Ra Applicati	aster scan and ions. 9
4 MICROL Microlithograp Nanolithograp	Electron proximity / Project	tion Printin ersion lithc aphy – M	g - Elec ography olecular	tron res – Se self-a	- sists T micor Issem	Electron otal Hrs ductor p bly nano	ron op Beam rocessi imprint	tics – Ra Applicati ng – M lithogra	aster scan and ons. 9 EMS design - phy - Dip-pen
4 MICROL Microlithograp Nanolithograp nanolithograp	Electron proximity / Project ITHOGRAPHY hy – Microchips - Imme hy - Nanosphere lithogr	tion Printin ersion lithc aphy – M	g - Elec ography olecular	tron res – Se self-a	sists - T micor Issem Ile 3D	Electron otal Hrs ductor p bly nano	ron op Beam rocessi imprint	tics – Ra Applicati ng – M lithogra design.	aster scan and ons. 9 EMS design - phy - Dip-pen
4 MICROL Microlithograp Nanolithograp 5 NANOLI Tools for nan	Electron proximity / Projec ITHOGRAPHY ohy – Microchips - Imme ohy - Nanosphere lithogr hy - Soft lithography - Ster	tion Printin ersion litho aphy – M eo -lithogra	g - Elec ography olecular uphy - Na	tron res – Se self-a anosca	sists - T micor Issem Ile 3D	- Electron otal Hrs ductor p bly nano shapes - otal Hrs	ron op Beam rocessii imprint - NEMS	tics – Ra Applicati ng – M lithogra design.	aster scan and ons. 9 EMS design - phy - Dip-pen 9
4 MICROL Microlithograp Nanolithograp 5 NANOLI Tools for nan	Electron proximity / Project ITHOGRAPHY ohy – Microchips - Imme ohy - Nanosphere lithogr hy - Soft lithography - Ster THOGRAPHY TOOLS olithography - Molecular m ching – Resist & imaging la	tion Printin ersion litho aphy – M eo -lithogra	g - Elec ography olecular uphy - Na	tron res – Se self-a anosca	sists - T micor Issem Ile 3D	- Electron otal Hrs ductor p bly nano shapes - otal Hrs	ron op Beam rocessii imprint - NEMS	tics – R Applicati ng – M lithogra design.	aster scan and ons. 9 EMS design - phy - Dip-pen 9
4 MICROL Microlithograp Nanolithograp nanolithograp 5 NANOLI Tools for nan- – Nano scrate	Electron proximity / Projec ITHOGRAPHY oby – Microchips - Imme oby - Nanosphere lithogr hy - Soft lithography - Ster THOGRAPHY TOOLS olithography - Molecular m shing – Resist & imaging la be taught	tion Printin ersion litho aphy – M eo -lithogra	g - Elec ography olecular uphy - Na	tron res – Se self-a anosca	sists - T micor Issem Ile 3D	- Electron otal Hrs ductor p bly nano shapes - otal Hrs	ron op Beam rocessii imprint - NEMS	tics – R Applicati ng – M lithogra design.	aster scan and ions. 9 EMS design - phy - Dip-pen 9 attern synthesis
4MICROLMicrolithograpNanolithograp5NANOLITools for nan- - Nano scratoTotal hours toReference(s)1James R	Electron proximity / Project ITHOGRAPHY oby – Microchips - Imme oby - Nanosphere lithogr hy - Soft lithography - Ster THOGRAPHY TOOLS olithography - Molecular m ching – Resist & imaging la be taught : . Sheats, Bruce W. Smith,	tion Printin ersion litho aphy – M eo -lithogra anipulation yers. "Microlitho	g - Elec ography olecular uphy - Na by STM graphy \$	tron re: – Se self-a anosca M and A	sists - T micor ssem lle 3D T AFM	- Electron Total Hrs Iductor p bly nano shapes - Total Hrs - LB film r - LB film r	ron op Beam rocessii imprint NEMS resists -	tics – R Applicati ng – M lithogra design. Nanopa	aster scan and ons. 9 EMS design - phy - Dip-pen 9 attern synthesis 45 ss, 1998.
4     MICROL       Microlithograp       Nanolithograp       5     NANOLI       Tools for nan- - Nano scrato       Total hours to       Reference(s)       1     James R       2     M.Gentill Ray Litho	Electron proximity / Project ITHOGRAPHY oby – Microchips - Imme oby - Nanosphere lithogr hy - Soft lithography - Ster THOGRAPHY TOOLS olithography - Molecular m shing – Resist & imaging la be taught : . Sheats, Bruce W. Smith, , Carlo Giovannella, Stefar ographies", 1 <sup>st</sup> edition, Spri	tion Printin ersion litho aphy – M eo -lithogra anipulation yers. "Microlitho no Selci, "N nger, 1994	g - Elec ography olecular uphy - Na by STM graphy s Janolitho	tron re: - Se self-a anosca M and A	sists - T micor Issem Ile 3D T AFM es and y: A B	- Electron otal Hrs ductor p bly nano shapes - otal Hrs - LB film r d Technol orderlanc	ron op Beam rocessii imprint NEMS esists - ogy", C	tics – R Applicati ng – M lithogra design. Nanopa K Nanopa 4 RC Pres en STM,	aster scan and ons. 9 EMS design - phy - Dip-pen 9 attern synthesis 15 5 5 5 EB, IB, and X-
4     MICROL       Microlithograp       Nanolithograp       5     NANOLI       Tools for name       - Nano scrator       Total hours to       Reference(s)       1     James R       2     M.Gentilin       3     P. Rai-C	Electron proximity / Project ITHOGRAPHY oby – Microchips - Imme oby - Nanosphere lithogr hy - Soft lithography - Ster THOGRAPHY TOOLS olithography - Molecular m obithography - Molecular m obithography - Molecular m be taught : . Sheats, Bruce W. Smith, , Carlo Giovannella, Stefan ographies", 1 <sup>st</sup> edition, Spri houdhury, "Handbook of m	tion Printin ersion litho aphy – M eo -lithogra anipulation yers. "Microlitho no Selci, "N nger, 1994 icrolithogra	g - Elec ography olecular uphy - Na by STM graphy S Nanolitho uphy, mio	tron re: - Se self-a anosca M and A Science ograph	sists - T micor Issem I <u>le 3D</u> T AFM - es and y: A B	- Electron otal Hrs ductor p bly nano shapes - otal Hrs - LB film r - LB film r d Technol orderlanc	ron op Beam rocessii imprint NEMS esists - ogy", C l betwe cro fabr	tics – R Applicati ng – M lithogra design. Nanopa KC Pres en STM, ication",	aster scan and ions. 9 EMS design - phy - Dip-pen 9 attern synthesis 15 ss, 1998. EB, IB, and X- IET, 1997.
4     MICROL       Microlithograp       Nanolithograp       5     NANOLI       Tools for name       - Nano scrato       Total hours to       Reference(s)       1     James R       2     M.Gentilin       3     P. Rai-C	Electron proximity / Project ITHOGRAPHY oby – Microchips - Imme oby - Nanosphere lithogr hy - Soft lithography - Ster THOGRAPHY TOOLS olithography - Molecular m ching – Resist & imaging la be taught : . Sheats, Bruce W. Smith, f, Carlo Giovannella, Stefan ographies", 1 <sup>st</sup> edition, Spri houdhury, "Handbook of m rner, "Nanotechnology an	tion Printin ersion litho aphy – M eo -lithogra anipulation yers. "Microlitho no Selci, "N nger, 1994 icrolithogra	g - Elec ography olecular uphy - Na by STM graphy S Nanolitho uphy, mio	tron re: - Se self-a anosca M and A Science ograph	sists - T micor Issem I <u>le 3D</u> T AFM - es and y: A B	- Electron otal Hrs ductor p bly nano shapes - otal Hrs - LB film r - LB film r d Technol orderlanc	ron op Beam rocessii imprint NEMS esists - ogy", C l betwe cro fabr	tics – R Applicati ng – M lithogra design. Nanopa KC Pres en STM, ication",	aster scan and ions. 9 EMS design - phy - Dip-pen 9 attern synthesis 15 ss, 1998. EB, IB, and X- IET, 1997.

	K.S. Ran	gasamy College of Tec	hnology -	Autono	mous	Regul				2008
Dep	artment	Nanoscience and Technology	Program			9	51 : N		Nanosc chnology	ience and
			S	Semeste	er II					
Ca	urse Code	Course Name	<u>^</u>	Hou	rs / We	ek	Credit		Maximu	m Marks
00		Course Marin	e	L	Т	Р	С	CA	ES	Total
	510206C	ADVANCED NANOBIOTECHNOLO		3	0	0	3	50	50	100
Ob	jective(s)	Understand the basic application of nanoma proteins, amino acids,	aterials in	biotechr	nology	and a	acquire th			
1	INTRODU	CTION				Т	otal Hrs		ę	9
Nuc nano	eis acids ostructured	areas of Biotech and and proteins refinement materials to basic and a	nt and ap	plicatior		nstrum	ients –			
2		ASE SYSTEMS					otal Hrs			9
		ems of devices for medi ics – Introduction – Lipid								
3	-	BASED NANOSTRUCT				-	otal Hrs			Э
bion	nolecular re	nanostructures building ecognition events – N organic nanoparticles – I	anobioelec	tronic						
4	DNA BASE	ED NANOSTRUCTURES	6			Т	otal Hrs		ę	9
	ugates of g	anostructures – Topogi old nanoparticles – DNA	oligomers			molec	ules in na			
5	-	ION OF NANOBIOTECH					otal Hrs		ę	9
optio		(metal) nanoparticles a n methods – Nanopartic esticides.								
Tota	I hours to b	e taught							4	5
Refe	erence(s) :									
1	CM, Nieme 2004.	eyer, C.A. Mirkin, "Nanol	piotechnolo	gy: Con	cepts,	Applic	cations ar	d Pers	pectives"	, Wiley – VCH,
2		o, "Nano: The Essentials"								
	Challe C	.S.R. Kumar, Josef		<b>A</b>					Tauran	<u> </u>
3		is, Techniques, Tools, A							Toward	as Biomedical

K.S. Ran	gasamy College of	Technolog	y - Auto	nomou	s Regul	ation		R 20	08	
Department	Nanoscience and Technology	Progran	n code 8	k Name		51 : M.Te		<ul> <li>Nanoscience and echnology</li> </ul>		
			Semest	erII						
Course Code	Course No.		Ho	ours / W	eek	Credit	M	aximum N	/larks	
Course Code	Course Nan	ne	L	Т	Р	С	CA	ES	Total	
08510207P	CHARACTERISATI NANOMATERIALS LABORATORY		0	0	3	2	50	50	100	
Objective(s)	Understand the difference characterisations of				niques a	nd acquire	knowle	dge on tl	ne various	
<ul> <li>Particle size of</li> <li>Determination</li> <li>Morphologica</li> <li>Surface Topo</li> <li>Identification</li> <li>Nano lithogram</li> </ul>	determination – XRD determination – (DLS n of surface area – po Il study of nano partic ographic study of Nan of functional group of uphy* ny one of the Researd	/ SLS) prosity - nar eles – SEM/ oparticles - nanopartic	TEM* AFM les - FT							
						Total Hrs		45		

K.S. Ra	angasamy Colle	-				Regu				2008
Department	Nanoscien		Pro	ogram co			51 : N			ience and
	Technol	ogy		Name Semest				lee	chnology	1
				1	rs / We	<u>al</u> (	Cradit		Maximu	
Course Code	e Cou	urse Name		L	T T	Р	Credit C	<u> </u>	ES	m Marks
	TECHNICA			L	I	Р	C	CA	ES	Total
08510208P		ION AND		0	0	2	0	100	00	100
Objective(s)	journals ar presentation	nd confere	nce pro e studen	ceeding ts.	s. To	impro	ve the	technic	al repo	icles in referred rt writing and
Methodology	<ul> <li>By area</li> <li>The public of the page rem</li> </ul>	dent. have to re ature. exposed wer poin minutes as make to hester. as to write review o	the facu efer the J to collect t, the stu discussi two pres e a Tech of researces	Ity guid lournals ot at lea ident ha on. entatior nical re ch pape ). The te	e will a and c st 20 s is to m is, one port fo r unde echnic	assign a t conference such Res hake pres e at the m r about 3 er various al report	e proce earch pa earch pa iddle ar 0-50 pa s subhea has to b	the gene edings a apers pu n for 15-2 nd the oth ages (Titla ading, Co o submitto	ral / subject and collect the blished in the 20 minutes her near the e page, One oncluding ed to the HOD y guide.	
	Week					Acti	vity			
	I	Allotment	of Facul	ty Guide	by the	HOD				
	II	Finalizing	the topic	c with the	e appro	val of I	Faculty G	Guide		
Execution	III-IV	Collection	n of Tech	nical pap	oers					
	V – VI	Mid seme	ester pres	sentation						
	VII – VIII	Report w	riting							
	IX	Report S	ubmissio	n						
	X-XI	Final pres	sentation							
		Continuou eek and 2	credits	ment						
			onent						ghtage	
Evaluation	Phase – I Pres					25 %				
	Phase – II Pres								25 %	
	Report prepara	ation and S	ubmissio	n				3	80 %	
	Final presenta	tion						2	20 %	
					Tota	ıl		1	00%	

K.S. Rang	gasamy College of Tecl	hnology - /	Autono	mous	Regul				2008
Department	Nanoscience and Technology	Program			e	51 : N		<ul> <li>Nanosc</li> <li>chnology</li> </ul>	ience and
		S	emeste	r III		-			
Course Code	Course Nom	<b>`</b>	Hou	rs / We	ek	Credit		Maximu	m Marks
Course Code	Course Name	;	L	Т	Р	С	CA	ES	Total
08510301C	NANODEVICES		3	0	0	3	50	50	100
Objective(s)	To understand the d nanodevices. To exp molecular and bioelect	lore the a	pplicatio	on of	nanod				
1 QUANTUM	I DEVICES				Т	otal Hrs			9
channel MOS T cellular Automa Quantum Parall		ansistor – E	lectron	wave t	transis it and	tor – Elec Qubit – C	ctron sp	in transision transision transision transition transiti transition transition transition transition transition transition	stor – Quantum Entanglement -
-	IG DEVICES ent – Tunnel Effect and					otal Hrs			9
Memory Applica RTBT Mobile – Coulomb Blocka	al Resonate Tunneling I ations – Basics Logic Cir - RTBT Threshold Gate ade- Performance – Te adder as an Example of a	cuits – Dyr – RTBT M echnology-	namic Lo Aultiplex Circui	ogic Ga er – S it Desi	ates - Single gn- W	Digital cir Electron riting and	cuits de Transi Driver	esign ba stor(SET 's – Log	sed on RTBT – ) – Principle – ic and Memory
	NDUCTING DEVICES A					otal Hrs			9
Flux Quantum of with Single Flux	neling Devices- Element device –LC –Gate – Mag devices – SFQD- RSFC of FET Electronics. Introd	netic Flux D – Applic	Quantui ation of	m – Qı super	uantur condu	n cellular cting dev	Automa vices –	ata- Qua Intergrat	ntum computer ed Electronices
	INTY OF NANODEVICE					otal Hrs	•		9
Dissipation – P. Thermal Noise- Equal Failure F Removal of unc of Nanoelectron		hiting Effect Factor – P Thermal I es – Unce	t – Limi hysical Noise –	ts due limits - Final	to Th - Ther Objec nosys	ermal Pa modynam ctives of tems- Un	nticle m nic Limi Integrat	notion- D ts - Rela ted Elec	Debye Length - ativistic Limits - troc Systems
	AR AND BIOELECTRO					otal Hrs			9
and nanotubes Information Pro	<ul> <li>molecular processor – polymer electronic – se pressing with chemical is projection- Synergy of</li> </ul>	elf Assembl reaction –	ling circ Nanom	uits – c	optical	molecula	r memo	ories – D	NA computer -
Total hours to b	e taught							2	15
Reference(s) :									
	P. Glosekotter and J. Quantum Devices", Spri			electro	onics a	and Nan	osysten	ns-From	Transistors to
	neault, Jean-Michel Lourt			nde, A	riel Le	venson, "	'Nanopl	hotonics	', ISTE.
3 W.R.Fahrn Springer, 2	er, "Nanotechnology and 2006.	d Nanoelec	tronics ·	– Mate	erials,	Devices a	and Me	asureme	ent Techniques

K.S. Ra	ingasamy Colleg	ge of Tecl	nnology ·	Auton	omous	Regul	ation		R	2008			
Department	Nanoscienc Technolo		Pro	gram co Name	de &		51 : N		<ul> <li>Nanosc</li> <li>chnology</li> </ul>	ience and			
		07	1	Semest	er III								
				Hou	rs/We	ek	Credit		Maximu	m Marks			
Course Code	e Cou	rse Name		L	Т	Р	С	CA	ES	Total			
08510304P				0	0	12	6	100	00	100			
Objective(s)						s. To provide exposure to the students to new a scientific problem in both practically and he department by the HOD							
Methodology	<ul> <li>By marea</li> <li>The public public</li></ul>	to the stu students h shed litera student is 5 years. g Power p 0 minutes student ha of the sem student ha Abstract,	ussions, f dent. ave to re ature. exposed oint, the s discussio as make tr lester. as to write review of st of Refe	the facul fer the J to collec student h n. wo prese a mini p f researc erences)	ty guide ournals at at leas has to m entation project r ch pape . The p	and c and c st 25 s nake p s, one eport r unde roject	ssign a t onferenc such Res resentati at the m for about r various report ha	opic in t e proce earch pa on for 1 iddle ar 30-50 p subhea s to be	he gener edings a apers pul 5-20 min nd the oth pages (Ti ading, Co submitte	d to the HOD			
	Week				,	Activity							
	1	Allotment	of Facult	ty Guide	by the		,						
		Finalizing	the topic	with the	approv	/al of I	Faculty G	iuide					
Execution	III-IV	Collection	n of Scier	tific pap	ers								
	V – VI	Mid seme	ester pres	entation									
	VII – VIII	Report w	riting										
	IX	Report S	ubmissior	า									
	X-XI	Final pres	sentation										
	- 100 %	Continuou		mont									
		Continuou eek and 2											
		-	onent						ghtage				
Evaluation	Phase – I Prese								25 %				
	Phase – II Pres	entation						2	25 %				
	Report preparat	tion and S	ubmissioi	ſ				3	80 %				
	Final presentati	on						2	20 %				
l					Tota			1	00%				

K.S. Ra	ngasamy Colle	ge of Techi	nology - Autonom		Regu				R 2008	
Department	Nanoscien Techno		Program code Name	&		51	: M.Tech	- Nanos chnolog		and
	Techno	logy	Semester I				16		) y	
				1	ours / \	Week	Credit	Ma	aximum	Marks
Course Code	e	Course N	ame	L	T	P	C	CA	ES	Total
08510305P	TECHNICA AND PRES		PREPARATION	0	0	2	0	100	00	100
Objective(s)	To provide	exposure to nd confere	the students to refence proceedings.							
Vlethodology	<ul> <li>By are</li> <li>The pub</li> <li>The last</li> <li>Usi follo</li> <li>The end</li> <li>The page rem</li> </ul>	mutual discu a to the stude students h slished litera student is 5 years. ng OHP/Por owed by 10 student ha of the sem student ha ge Abstract, narks and Li	ave to refer the Jou ture. exposed to collect a wer point, the stude minutes discussion s make two present	guid rnals It lea It le	e will s and ast 20 as to r ns, on port fo er und echnic	assign confere such R nake p e at the or abou er vario cal repo	a topic in ence proce research p resentatio e middle a ut 30-50 p bus subhe ort has to	the gen eedings papers on for 15 and the ages (T eading, b subm	s and co publish 5-20 mi other n Title pag Conclu itted to	ollect the ed in the nutes ear the ge, One ding the HOI
	Week				Acti	vity				
		Allotment	of Faculty Guide by	the		.,				
	II		the topic with the ap			Faculty	/ Guide			
Execution	III-IV	Collection	of Technical papers	S						
	V – VI	Mid seme	ster presentation							
	VII – VIII	Report wri	•							
	IX	Report Su	bmission							
	X-XI	Final pres	entation							
		-								
		Continuous eek and 2 c	Assessment redits							
		Compo	onent					eightage	;	
Evaluation	Phase – I Pres							25 %		
	Phase – II Pres	sentation					:	25 %		
	Report prepara	ation and Su	bmission				;	30 %		
	Final presentat	ion					2	20 %		
· ·							0.001	00%		

K.S. Ra	ingasamy Colle	ge of Tecl				Regu				2008
Department	Nanoscien Technol		Prog	ram co Name	de &		51 : N			ience and
	Technol	ogy	S	Semeste	er IV			Te	chnology	·
• • •				Но	urs / We	ek	Credit		Maximu	m Marks
Course Code	e Co	urse Name	;	L	Т	Р	С	CA	ES	Total
08510401P	PROJECT	WORK - P	HASE II	0	0	40	20	50	50	100
Objective(s)						•				tudents to nev theoretically
Methodology	<ul> <li>By are</li> <li>The pub</li> <li>The lass</li> <li>Usi by</li> <li>The end</li> <li>The end</li> <li>The end</li> <li>The end</li> </ul>	a to the stu e students blished liter e student is t 5 years. ng Power p 10 minutes e student h d of the ser e student h ge Abstract	cussions, t udent. have to ref ature. s exposed t coint, the s discussion as make two nester. as to write , review of List of Refe	he facu fer the s to colle student n. wo pres a proje resear erences	Ity guid Journals ct at lea has to r entation ect repo ch pape ). The p	e will a s and o ist 50 make p ns, on rt for a er und project after	assign a conference such Res presentat e at the n about 30- er various report ha the appro	topic in ce proce search p tion for niddle a 50 page s subhe as to be	the gene eedings a papers pu 15-20 mi nd the of es (Title p ading, C	oncluding ed to the HOD
	Week					Acti	vity			
			of Faculty					No. 1 al a		
Evenution	    - V	-	the topic			/al of I	Faculty G	suide		
Execution	V – VI		ester prese							
	VII – VIII	Report w	-	mation						
	IX	•	ubmission							
	X-XI	Final pres								
L										
		Continuous week and	20 credits	ent an	d 50 %	End s	emester			
	Diana 10	-	onent						ightage	
Evaluation	Phase – I Pres								5%	
	Phase – II Pres		ula maio alta t						5 %	
	Report prepara	ation and S	upmission						20 %	
	Viva - Voce				<del>-</del>				50 %	
					Tota	1		1	00%	

	K.S. Ra	ngasamy College of Tecl	hnology - <i>I</i>	Autono	mous	Regul	ation		R	2008
Depar	tment	Nanoscience and Technology	Program			;	51 : N		· Nanosc chnology	ience and
				Elective	e l					
Cou		Course Name		Hou	rs / We	ek	Credit		Maximu	m Marks
Co	de	Course Marine		L	Т	Р	С	CA	ES	Total
08510		MICRO ELECTRO MECI SYSTEMS (MEMS) AND ELECTROMECHANICAL SYSTEMS (NEMS)	NANO -	3	0	0	3	50	50	100
Objecti	ive(s)	To explore the knowled fabrication and applicati design. To explore the b application of NEMS & M	on of MEN asic princip	/IS. To	study	the p	roperties	of mat	terials us	sed for MEMS
1 P0	OTENT	IAL OF SILICON TECHNO	DLOGY			Т	otal Hrs		ę	9
technic 2 M technic crystal microsy packag	IICRO E Silicor Ques – reactiv ystem ging –	ilicon technology – limits micromechanics for nanoe ELECTRO MECHANICAL micromachining – bulk photolithography – ion im /e etching – LIGA – x-r packaging – device leve packaging technology –	Ictronics – i SYSTEMS micromach plantation ay based el packagin	ntegrate (MEMS ining – – diffusi fabricat g – sy	ed opto ) surfac ion – c ion – rstem	electr T e mic oxidati packa level	onics. otal Hrs romachin on – CVI aging of packaging	ing - M D – PV MEMS g – int	licrosyste D – spu devices erface i	9 ems fabrication ttering – single – three level n microsystem
	ging ma	terials. ALS AND DESIGN OF ME	MS			т	otal Hrs			9
metals	Single silicon Desig olithogra	e crystal silicon - Poly sili carbide-diamond - III-V ma n – considerations – selec	icon – silic aterials – pi	iezoelec	ctric ma	silicon aterials	nitride – s.	uring pr		ased materials-
		anical stress analysis - dy	- geometry	y shapir	ng – me	echan				hanical loading
method	ds – cor	anical stress analysis – dy mputer aided designing.	<ul> <li>geometry</li> <li>ynamic ana</li> </ul>	y shapir	ng – me	echan cial fra	acture an		- mecha	hanical loading
method4Alcapacitplatform	ds – cor PPLICA Inertia tive - n m – opti	anical stress analysis – dy mputer aided designing. TION OF MEMS AND NE al sensors – acceleromete nicro robotics – micro cha ical data switching – RF M	– geometry ynamic ana MS er – gyrosca annel heat EMS – ME	y shapir Ilysis – ope - m sinks – MS vari	ng – me interfa nicrome	echan cial fra T echani al MEI apacito	acture an fotal Hrs cal press MS – vis prs – MEN	alysis - ure sei ual disj	- mecha sors – p play – p ches – R	hanical loading nical designing 9 Dizo resistive – recision optical Resonators.
method4Alcapacitplatform	ds – cor PPLICA Inertia tive - n m – opti ANO EI	anical stress analysis – dy mputer aided designing. TION OF MEMS AND NE al sensors – acceleromete nicro robotics – micro cha ical data switching – RF M LECTROMECHANICAL S	– geometry ynamic ana MS er – gyrosc annel heat EMS – ME YSTEMS (N	y shapir Ilysis – ope - m sinks – <u>MS vari</u> NEMS)	ng – mo interfa nicromo optica able ca	echan cial fra T echani al MEI apacito T	acture an otal Hrs cal press MS – vis prs – MEN otal Hrs	alysis - ure ser ual disj <u>//S swit</u>	- mecha sors – j blay – p ches – R	hanical loading nical designing 9 bizo resistive – recision optical lesonators. 9
method4Alcapacitplatform5N/electroion bea	ds – cor PPLICA Inertia tive - n m – opti ANO EI Introd mechar am dop	anical stress analysis – dy mputer aided designing. TION OF MEMS AND NE al sensors – acceleromete nicro robotics – micro cha ical data switching – RF M	– geometry ynamic ana MS er – gyrosc annel heat EMS – ME YSTEMS (N ng of NE - nano imp	y shapir Ilysis – ope - m sinks – <u>MS vari</u> NEMS) MS ba rint litho	ng – mo interfa nicrome optica able ca ased p ography	echan cial fra echani al MEI apacito T upon y – pc	acture an otal Hrs cal press MS – vis ors – MEN otal Hrs electron olymeric r	alysis - ure ser ual disp //S swit beam ano fib	- mecha sors – j olay – p ches – R lithogra er templ	hanical loading nical designing bizo resistive – recision optical desonators. b aphy – Nano ates – focused
method4Alcapacitplatform5Naelectroion beafuture of	ds – cor PPLICA Inertia tive - n m – opti ANO EI Introd pmechar am dop challeng	anical stress analysis – dy mputer aided designing. TION OF MEMS AND NE al sensors – accelerometer nicro robotics – micro cha ical data switching – RF M LECTROMECHANICAL S' uction – nano machini nical systems fabrication - ing wet chemical etching	– geometry ynamic ana MS er – gyrosco annel heat EMS – ME YSTEMS (N ng of NE - nano imp	y shapir Ilysis – ope - m sinks – <u>MS vari</u> NEMS) MS ba rint litho	ng – mo interfa nicrome optica able ca ased p ography	echan cial fra echani al MEI apacito T upon y – pc	acture an otal Hrs cal press MS – vis ors – MEN otal Hrs electron olymeric r	alysis - ure ser ual disp //S swit beam ano fib	- mecha sors – j blay – p ches – R g lithogra er templ arge sca	hanical loading nical designing bizo resistive – recision optical desonators. b aphy – Nano ates – focused
method4Alcapacitplatform5N/electroion beafuture ofTotal h	ds – cor PPLICA Inertia tive - n m – opti ANO EI Introd pmechar am dop challeng	anical stress analysis – dy mputer aided designing. TION OF MEMS AND NE al sensors – accelerometer nicro robotics – micro cha ical data switching – RF M LECTROMECHANICAL S' uction – nano machini nical systems fabrication – ing wet chemical etching ges - applications. be taught	– geometry ynamic ana MS er – gyrosco annel heat EMS – ME YSTEMS (N ng of NE - nano imp	y shapir Ilysis – ope - m sinks – <u>MS vari</u> NEMS) MS ba rint litho	ng – mo interfa nicrome optica able ca ased p ography	echan cial fra echani al MEI apacito T upon y – pc	acture an otal Hrs cal press MS – vis ors – MEN otal Hrs electron olymeric r	alysis - ure ser ual disp //S swit beam ano fib	- mecha sors – j blay – p ches – R g lithogra er templ arge sca	hanical loading nical designing Dizo resistive – recision optical desonators. Diaphy – Nano ates – focused le integration –
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K.S. Ra	angasamy College of Tec	hnology -	Autono	mous	Regul	ation		R	2008	
Department	Nanoscience and Technology	Program code & Name				51 : M.Tech - Nanoscience and Technology				
			Elective	e				0)		
Hours / Week Credit Maximum Ma								m Marks		
Course Cod	e Course Nam	Course Name		Т	Р	С	CA	ES	Total	
08510342E						100				
Objective(s)	Objective(s) To provide exposure to the students on biophysics in nanotechnology. To explore the can therapy and drug delivery system. To study the various devices used for nanotechnology									
1 IMAGING TECHNIQUES Total Hrs 9									9	
Medical diagnostics - Imaging - MRI - Principal, Instrumentation, Operation and Imaging - NMR - Principal,										
Instrumentation, Operation and imaging - Nanotechnology based diagnostics including imaging - Applications.										
	IOACTIVE GLASSES	Duenenetie		الم م ما م		otal Hrs			) Dronortion	
	Nano Bioactive glasses - neasurement of bioactivity cations.									
3 CANCE	R TREATMENT				Т	otal Hrs		ç	9	
Immunotherapy – Vaccine immunotherapy – Radiotherapy – Thermotherapy – Photo dynamic therapy – Nance particulate targeting.         4       DRUG DELIVERY       Total Hrs       9         Introduction, Antibody conjugated nanoparticles – Conjugated nanoparticles interaction with biological surfaces – Biomedical nanoparticles – Liposomes - Dentrimers - Different types of drug loading, drug release and							ogical surfaces			
	e polymers – Applications.				-					
	5         NANOSENSORS         9           ntroduction to nano sensors – Organization techniques – Ion sensing at nano particle surface – cation sensing									
- anion sens	ing – surface confined ch g – Raman sensing at surf	emical sen	sors – r	nanopa	article	sensors	<ul> <li>calori</li> </ul>	metric se	ensing - vapor	
Total hours to be taught 45						5				
Reference(s)	:									
1 Dimiter S. Dimitrov, Colloids and Surfaces A: Physicochem. Eng. Aspects										
2 James A. Schwarz, Cristian I. Contescu, Karol Putyera, "Dekker encyclopedia of nanoscience and nanotechnology" CRC Press, 2004.										
	Natalie P. Praetorius and Tarun K. Mandal, Recent Patents on Drug Delivery & Formulation									
<sup>4</sup> Oncol	Uncol									
5 Y. Lu, S.C. Chen, "Micro and nano-fabrication of biodegradable polymers for drug delivery" Advanced Drug Delivery Reviews, 56 (1621-1633) 2004.										
	Wei Xia and Jiang Chang, Preparation and characterization of nano-bioactive-glasses (NBG) by a quick alkali-mediated sol-gel method, Materials letters, 61 (3251-3253) 2007.									

K.S. Rangasamy College of Technology - Autonomous Regulation R 2008									
Department         Nanoscience and Technology         Program code & Name         51 : M.Tech - Nanoscience and Technology									
Elective II									
Course Code Course Name		Hou	rs / We	ek	Credit	Credit Maximum Marks			
			L	Т	Р	С	CA	ES	Total
08510351E	NANOSAFETY AND ENVIRONMENTAL ISSU		3	0	0	3	50	50	100
Objective(s) To provide exposure to the students on safety and environmental issues of nano science and technology. To explore the toxic effects of nanotechnology on human health and life. To analyze the various issues on environmental effects and explore suitable remedial measures.									
	ETY - INTRODUCTION					otal Hrs			9
Identification of Nano - Specific Risks- Responding to the Challenge -Human health hazard – Risk reduction – Standards – Safety – transportation of NP– Emergency responders. Risk assessment –Environmental Impact – Predicting hazard – Materials Characterization. Risk Assessment related to nanotechnology – Environmental and policy making- Ecotoxicity measurement of Polychlirinated biphenyl and intermediates in their degradation2NANOTOXICOLOGY9Inhalation of nanomaterials – Overview. Introduction- Inhalation deposition and Pulmonary clearance of Insoluble Solids – Bio –persistence of Inhaled solid material. Systemic Trenslocation of inhaled Particles.									
	ects of SWCNT- Pulmor Immation with oxidative st								Interactions of
	ENTAL AND FIELD ISSU		laotione			otal Hrs	lopnag		9
Nanoparticle exposure and systematic cardiovascular effects – experimental data – respiratory particulate matter exposure and cardiovascular toxicity, Nanoparticles – Hypothesis and research approaches. SWCNT – Experimental data. Toxicity of polymeric nanoparticles with respect to their application as drug carriers. Particle exposure through the indoor air environment –Measurement of indoor of PM and experimental study.         4       NANOSAFETY       Total Hrs       9         Needs for regulations, training and education for health protection and environmental security of nanotechnologies – definitions and essence – general benefits – benefits for health and medical practice – potential risks – The approaches to assessment of exposure to the nanotechnology. Bioethics and legal aspects of potential health and environmental risks in nanotechnology – Legal regulatory considerations of nanotechnology.									
	GES AND FUTURES					otal Hrs			9
Nanotechnology – the frame of worker training, public education, and participation – Introduction – Nanotoxicity – Workers protection – International documents – protection of medical staff – Nurses education – Public information. Occupational risk assessment and management – focus on nanomaterials.									
Total hours to b	be taught							4	15
Reference(s) :									
P.P. Simeonova, N. Opopol and M.I. Luster, "Nanotechnology - Toxicological Issues and Environmental Safety", Springer 2006.									
2 Vinod Labhasetwar and Diandra L. Leslie, "Biomedical Applications of nanotechnology", A John Willy & son Inc,NJ, USA, 2007.									
3 Miyawaki, J.; <i>et.al</i> Toxicity of Single-Walled Carbon Nanohorns. <i>ACS Nano 2</i> (213–226) 2008.									
4 Hutchison, J. E. Green Nanoscience: A Proactive Approach to Advancing Applications and Reducing Implications of Nanotechnology. <i>ACS Nano 2</i> , (395–402) 2008.									
5 Mo-Tao Zhu <i>et.al</i> Comparative study of pulmonary responses to nano- and submicron-sized ferric oxide in rats Toxicology, 21 (102-111) 2008.									
6 Dracy J. Gentleman, Nano and Environment: Boon or Bane? Environmental Science and technology, 43 (5), P1239, 2009.									

	K.S. Ran	gasamy College of Tech	nnology - J	Autono	mous	Regul	ation		F	R 2008		
Dep	epartment Nanoscience and Program code & Na			Name	e 51 : M.Tech - Nanoscience and Technology							
				Elective								
Cau	rse Code	Course Name	Hou	Hours / Week		Credit	Maximum Marks					
Cou	ise Code	Course Marine		L	Т	Р	С	CA	ES	Total		
085	10352E INTELLECTUAL PROPERTY RIGHTS		ERTY	3	0	0	3	50	50	100		
Obj	Dbjective(s) To provide awareness about IP Rights. To provide exposure to protect the Intellectu property.									the Intellectual		
1	INTRODUCTION						Total Hrs 9					
Introduction - Invention and Creativity - Intellectual Property (IP) - Importance - Protection of IPR - Basic types of property (i. Movable Property ii. Immovable Property and iii. Intellectual Property).												
2	-	REGISTRATION					otal Hrs		9			
IP - Patents - Copyrights and related rights - Trade Marks and rights arising from Trademark registration - Definitions - Industrial Designs and Integrated circuits - Protection of Geographical Indications at national and International levels - Application Procedures.												
3		TUAL PROPERTY					Total Hrs 9					
International convention relating to Intellectual Property - Establishment of WIPO - Mission and Activities - History - General Agreement on Trade and Tariff (GATT).												
4	STRATEG					Total Hrs 9				•		
		Vs WTO and Strategies of a national Intellectual P								Ordinance and		
5	CASE STUDIES					-	Total Hrs			9		
		on - Patents (Basumati rio in and Integrated circuits -										
Tota	otal hours to be taught						45					
Refe	erence(s) :											
1	1 N.R. Subbaram," Handbook of Indian Patent Law and Practice ", S. Viswanathan (Printers and Publishers) Pvt. Ltd., 1998.											
2	Eli Whitney, United States Patent Number: 72X, Cotton Gin, March 14, 1794.											
3	Intellectual Property Today: Volume 8, No. 5, May 2001, [www.iptoday.com].											